# **VS-ST300CL Series**

Vishay Semiconductors



# Phase Control Thyristors (Hockey PUK Version), 560 A



B-PUK (TO-200AC)

PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub>	560 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	400 V, 800 V, 1200 V, 1600 V, 1800 V, 2000 V				
V <sub>TM</sub>	2.18 V				
I <sub>GT</sub>	100 mA				
TJ	-40 °C to +125 °C				
Package	B-PUK (TO-200AC)				
Circuit configuration	Single SCR				

#### **FEATURES**

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC)
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

## **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATING	MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		560	A			
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	C°			
1		1115	A			
IT(RMS)	T <sub>hs</sub>	25	°C			
	50 Hz	8000	۵			
ITSM	60 Hz	8380	A			
l <sup>2</sup> t	50 Hz	320	kA <sup>2</sup> s			
1-1	60 Hz	292	KA-S			
V <sub>DRM</sub> /V <sub>RRM</sub>		400 to 2000	V			
t <sub>q</sub>	Typical	100	μs			
TJ		-40 to 125	O°			

## **ELECTRICAL SPECIFICATIONS**

VOLTAGE R	VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I <sub>DRM</sub> /I <sub>RRM</sub> MAXIMUM AT T <sub>J</sub> = T <sub>J</sub> MAXIMUM mA				
	04	400	500					
	08	800	900					
VS-ST300CL	12	1200	1300	50				
V0 010000E	16	1600	1700	00				
	18	1800	1900					
	20	2000	2100					

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COMPLIANT

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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS
Maximum average on-state current	1	180° condu	ction, half sine v	vave	560 (275)	А
at heatsink temperature	I <sub>T(AV)</sub>	double side	(single side) co	oled	55 (75)	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	1115	
		t = 10 ms	No voltage		8000	
Maximum peak, one-cycle	I	t = 8.3 ms	reapplied		8380	А
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		6730	kA <sup>2</sup> s
		t = 8.3 ms	and a second second	Sinusoidal half wave, initial $T_J = T_J$ maximum	7040	
Maria 2 factoria		t = 10 ms	No voltage reapplied		320	
	l <sup>2</sup> t	t = 8.3 ms			292	
Maximum I <sup>2</sup> t for fusing	1-1	t = 10 ms	100 % V <sub>RRM</sub>		226	
		t = 8.3 ms	reapplied		207	
Maximum I <sup>2</sup> $\sqrt{t}$ for fusing	l²√t	t = 0.1 to 10	) ms, no voltage	reapplied	3200	kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.97	v
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$			v
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), T <sub>J</sub> = T <sub>J</sub> maximum			0.74	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi x I_{T(AV)}), T_J = T_J maximum$			0.73	11152
Maximum on-state voltage	V <sub>TM</sub>	$I_{pk}$ = 1635 A, $T_J$ = $T_J$ maximum, $t_p$ = 10 ms sine pulse			2.18	V
Maximum holding current	Ι <sub>Η</sub>	T _ 25 °C	anada aupply 1	2. V registive load	600	<b>m A</b>
Typical latching current	١L	T <sub>J</sub> = 25 °C, anode supply 12 V resistive load 1000		1000	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,t_r \leq 1~\mu s$ $T_J$ = $T_J$ maximum, anode voltage $\leq 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t <sub>d</sub>	Gate current 1 A, dl <sub>g</sub> /dt = 1 A/ $\mu$ s V <sub>d</sub> = 0.67 % V <sub>DRM</sub> , T <sub>J</sub> = 25 °C	1.0	
Typical turn-off time	t <sub>q</sub>	$I_{TM}$ = 550 A, $T_J$ = $T_J$ maximum, dl/dt = 40 A/µs, $V_R$ = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ $t_p$ = 500 µs	100	μs

BLOCKING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$	500	V/µs			
Maximum peak reverse and off-state leakage current	I <sub>RRM,</sub> I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	50	mA			



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TRIGGERING						
DADAMETED	SYMBOL			VALUES		UNITS
PARAMETER	STINDUL		ST CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	10	0.0	w
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	vv
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	3	.0	А
Maximum peak positive gate voltage	+ V <sub>GM</sub>	T T movimum			20	v
Maximum peak negative gate voltage	- V <sub>GM</sub>	$I_{J} = I_{J}$ maximum,	$T_J = T_J$ maximum, $t_p \le 5$ ms			v
		T <sub>J</sub> = - 40 °C		200	-	
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Maximum required gate trigger/	100	200	mA
		T <sub>J</sub> = 125 °C	current/voltage are the lowest	50	-	
		T <sub>J</sub> = - 40 °C	value which will trigger all units	2.5	-	
DC gate voltage required to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.8	3.0	V
		T <sub>J</sub> = 125 °C		1.1	-	
DC gate current not to trigger	I <sub>GD</sub>		Maximum gate current/	10.0		mA
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J$ maximum	voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.25		v

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to 125	°C		
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150	°C		
Maximum thermal registeries, junction to besteink	Р	DC operation single side cooled	0.11			
Maximum thermal resistance, junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.05	K/W		
Maximum thermal registeres, asso to bestaink	Р	DC operation single side cooled	0.011	r∿ vv		
Maximum thermal resistance, case to heatsink	$R_{\text{thC-hs}}$	DC operation double side cooled	0.006			
Mounting force, ± 10 %			9800 (1000)	N (kg)		
Approximate weight			250	(kg) g		
Case style		See dimensions - link at the end of datasheet	B-PUK (TO-2	200AC)		

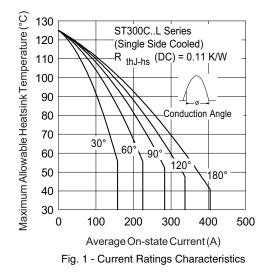
CONDUCTION ANGLE	SINUSOIDAL	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		UNITS	
CONDOCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS	
180°	0.012	0.010	0.008	0.008	T <sub>J</sub> = T <sub>J</sub> maximum		
120°	0.014	0.015	0.014	0.014			
90°	0.018	0.018	0.019	0.019		K/W	
60°	0.026	0.027	0.027	0.028			
30°	0.045	0.046	0.046	0.046			

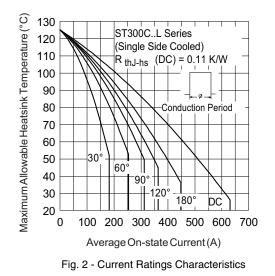
Note

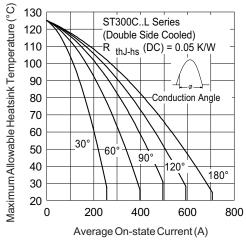
• The table above shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC

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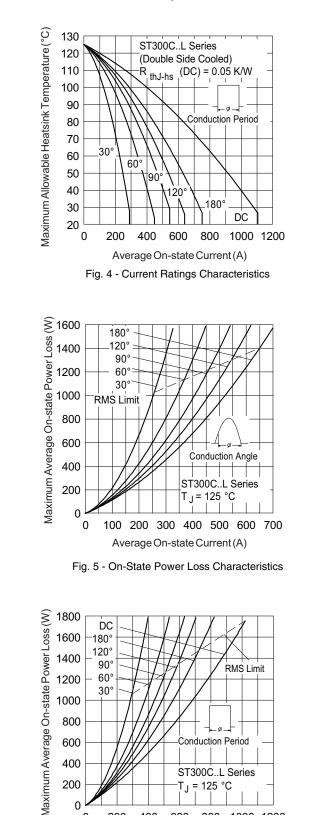






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0

0

200

400

600

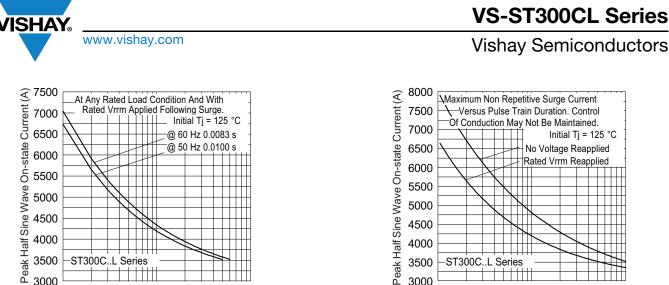
Average On-state Current (A)

Fig. 6 - On-State Power Loss Characteristics

800 1000 1200

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100



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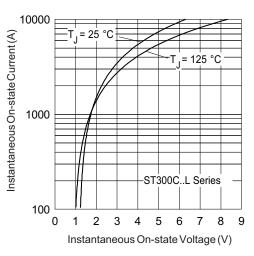
0.01 0.1 Pulse Train Duration (s) Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

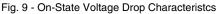
ST300C..L Series

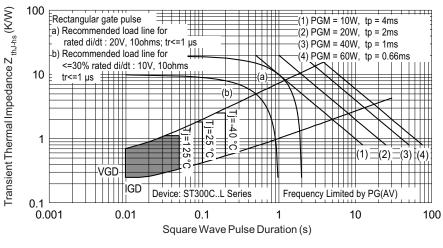
4500 4000

3500

3000









ST300C..L Series

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Fig. 7 - Maximum Non-Repetitive Surge Current

Single and Double Side Cooled

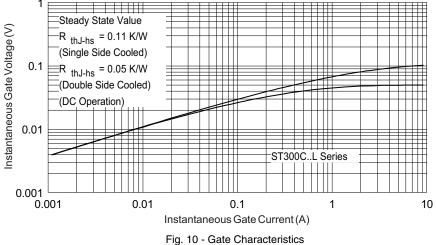
Number Of Equal Amplitude Half Cycle Current Pulses (N)

3000

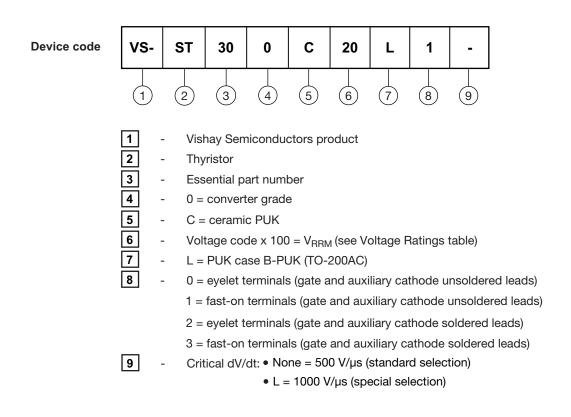
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### **ORDERING INFORMATION TABLE**



LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?95076				

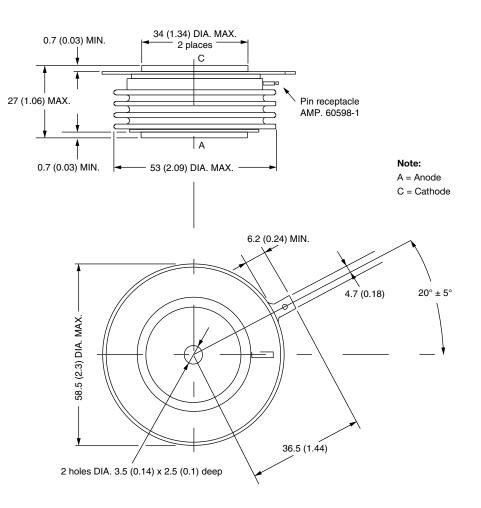
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# **B-PUK (TO-200AC)**

#### **DIMENSIONS** in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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